

BRS

ISNR

Pending

00:11: (0) 63 and ('HCl' hydrogen adj chloride hydrochloric)

Active

L19: (1529) (plasma with ('HCl' hydrogen adj chloride hydrochloric))

L20: (737) plasma with (nonferromagnetic antiferromagnetic non-ferromagnetic nonmagnetic non-m...)

L21: (16722) plasma with (ferrimagnetic magnetic magnetic magneticresistive magnetization)

L27: (17) 26 and ('NiFe' 'CoFe' 'NiFeCo' 'Ru')

L51: (694) ('PtMn' 'IrMn')

L57: (366) 19 and (plasma adj etch\$3)

L58: (103) 57 and (ferrimagnetic magnetic magnetic magneticresistive magnetization)

L59: (24) 57 and ((ferrimagnetic magnetic magneticresistive magnetization) with (layer film m...)

L60: (1) 19 and 20

L61: (34) 19 and (nonferromagnetic antiferromagnetic non-ferromagnetic nonmagnetic non-magnetic)

L63: (316) 20 and 21

L64: (26) 63 and ('HCl' hydrogen adj chloride hydrochloric)

L66: (1) ("6491832").PN.

L67: (1) ("4439294").PN.

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 Plurals Highlight all hit terms initially63 and ('HCl'
hydrogen adj
chloride
hydrochloric)

U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	R

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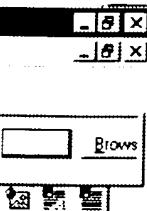
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L67: (1) ("4439294").PN.

L68: (26) 63 and ('HCl' hydrogen adj chloride hydrochloric)

Failed



	U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
1	<input type="checkbox"/>	<input type="checkbox"/>	US 6254721 B1	20010703	29	Method and apparatus for processing samples	156/345.22	134/1.3; 156/345.31;
2	<input type="checkbox"/>	<input type="checkbox"/>	US 6106895 A	20000822	9	Magnetic recording medium and process for producing the same	427/129	427/387
3	<input type="checkbox"/>	<input type="checkbox"/>	US 6077788 A	20000620	28	Method and apparatus for processing samples	438/706	438/710
4	<input type="checkbox"/>	<input type="checkbox"/>	US 6036816 A	20000314	30	Apparatus for processing a sample having a metal laminate	156/345.22	134/1.3; 156/345.31
5	<input type="checkbox"/>	<input type="checkbox"/>	US 5976257 A	19991102	60	Apparatus for continuously forming a large area deposited film by means of	118/718	118/723MA;
6	<input type="checkbox"/>	<input type="checkbox"/>	US 5952245 A	19990914	28	Method for processing samples	438/720	118/729; 134/1.2;
7	<input type="checkbox"/>	<input type="checkbox"/>	US 5922454 A	19990713	17	Magnetic recording medium	428/328	438/718 428/329;
8	<input type="checkbox"/>	<input type="checkbox"/>	US 5908683 A	19990601	21	Magnetic recording medium	428/141	428/330; 428/328;
9	<input type="checkbox"/>	<input type="checkbox"/>	US 5888338 A	19990330	38	Magnetron plasma processing apparatus and processing method	156/345.46	428/329; 118/723E
10	<input type="checkbox"/>	<input type="checkbox"/>	US 5876833 A	19990302	16	Magnetic recording medium containing magnetic powder and a poly	428/141	428/328; 428/329;
11	<input type="checkbox"/>	<input type="checkbox"/>	US 5868854 A	19990209	32	Method and apparatus for processing samples	134/1.3	134/1.2; 438/704;
12	<input type="checkbox"/>	<input type="checkbox"/>	US 5848684 A	19981215	8	Method for transporting magnetic	198/805	198/690.1; 210/622

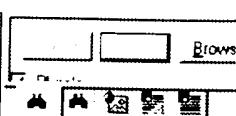
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L67: (1) ("4439294").PN.

L68: (26) 63 and ('HCl' hydrogen adj chloride hydrochloric)

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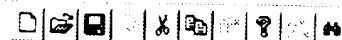


	U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
13	<input type="checkbox"/>	<input type="checkbox"/>	US 5718964 A	19980217	23	Magnetic recording medium	428/141	428/323;
14	<input type="checkbox"/>	<input type="checkbox"/>	US 5637393 A	19970610	15	Magnetic recording medium and its manufacturing method	428/332	428/328;
15	<input type="checkbox"/>	<input type="checkbox"/>	US 5540957 A	19960730	14	Method of manufacturing a magnetic recording medium	427/535	428/408;
16	<input type="checkbox"/>	<input type="checkbox"/>	US 5496607 A	19960305	23	Magnetic recording medium	428/65.3	427/131;
17	<input type="checkbox"/>	<input type="checkbox"/>	US 5352501 A	19941004	36	Longitudinal magnetic recording medium comprising a circumferential Dry etching method	428/65.7	427/576;
18	<input type="checkbox"/>	<input type="checkbox"/>	US 5320707 A	19940614	36		216/69	428/336;
19	<input type="checkbox"/>	<input type="checkbox"/>	US 5080971 A	19920114	23	Magnetic recording medium	428/336	428/694B;
20	<input type="checkbox"/>	<input type="checkbox"/>	US 5069967 A	19911203	23	Magnetic recording medium	428/336	428/336;
21	<input type="checkbox"/>	<input type="checkbox"/>	US 5057623 A	19911015	18	Organic fluorine compound	564/82	427/409;
22	<input type="checkbox"/>	<input type="checkbox"/>	US 4971880 A	19901120	14	Developer containing halogenated amorphous carbon particles prepared	430/111.34	427/132;
23	<input type="checkbox"/>	<input type="checkbox"/>	US 4966648 A	19901030	10	Process for producing thin film magnetic head	216/22	564/153;
24	<input type="checkbox"/>	<input type="checkbox"/>	US 4911812 A	19900327	8	Plasma treating method and apparatus	204/192.32	564/157;

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LS7: (366) 19 and (plasma adj etch\$3)

LS8: (103) 57 and (ferrimagnetic magnetic magnetic magnetic magnetic resistive magnetization)

LS9: (24) 57 and ((ferrimagnetic magnetic magnetic resistive magnetization) with (layer film m...)

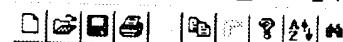


	U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
1	<input type="checkbox"/>	<input type="checkbox"/>	US 20030013314	20030116	18	Method of reducing particulates in a plasma etch chamber during a metal e	438/710	
			A1					
2	<input type="checkbox"/>	<input type="checkbox"/>	US 20020142572	20021003	45	Method for forming metallic film and apparatus for forming the same	438/586	438/584
			A1					
3	<input type="checkbox"/>	<input type="checkbox"/>	US 20020129900	20020919	16	Method for processing specimens, an apparatus therefor and a method of m	156/345.31	156/345.32
			A1					
4	<input type="checkbox"/>	<input type="checkbox"/>	US 20020072228	20020613	7	Semiconductor conductive pattern formation method	438/669	
			A1					
5	<input type="checkbox"/>	<input type="checkbox"/>	US 6526996 B1	20030304	8	Dry clean method instead of traditional wet clean after metal etch	134/1.3	134/1.2;
								134/26;
6	<input type="checkbox"/>	<input type="checkbox"/>	US 6507187 B1	20030114	9	Ultra-sensitive magnetoresistive displacement sensing device	324/207.21	324/207.26;
								324/252;
7	<input type="checkbox"/>	<input type="checkbox"/>	US 6491832 B2	20021210	15	Method for processing specimens	216/22	216/67;
								216/75;
8	<input type="checkbox"/>	<input type="checkbox"/>	US 6440863 B1	20020827	14	Plasma etch method for forming patterned oxygen containing plasma e	438/710	438/711;
								438/717;
9	<input type="checkbox"/>	<input type="checkbox"/>	US 6277752 B1	20010821	12	Multiple etch method for forming residue free patterned hard mask layer	438/692	438/700;
								438/706;
10	<input type="checkbox"/>	<input type="checkbox"/>	US 6069035 A	20000530	12	Techniques for etching a transition metal-containing layer	438/220	438/720
11	<input type="checkbox"/>	<input type="checkbox"/>	US 5892706 A	19990406	43	Fram, fram card, and card system using the same	365/145	365/226;
								365/65
12	<input type="checkbox"/>	<input type="checkbox"/>	US 5798964 A	19980825	43	FRAM, FRAM card, and card	365/145	365/149;

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✓ L57: (366) 19 and (plasma adj etch\$3)

✓ L58: (103) 57 and (ferrimagnetic magnetic magnetic magnetic magnetic resistive magnetization)

✓ L59: (24) 57 and ((ferrimagnetic magnetic magnetic resistive magnetization) with (layer film m...)

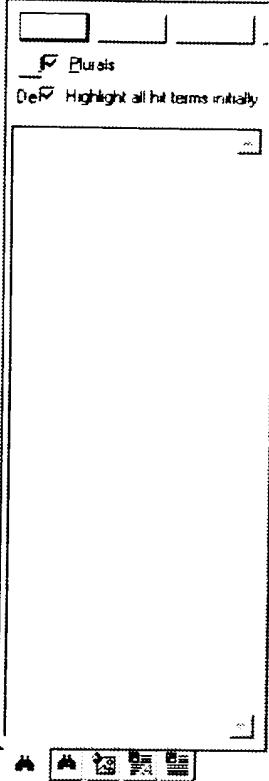


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13	<input type="checkbox"/>	US 5429710 A	19950704	9	Dry etching method	438/714	216/17;
14	<input type="checkbox"/>	US 5368684 A	19941129	9	Etching method for a silicon-containing layer using hydrogen	438/719	216/41;
15	<input type="checkbox"/>	US 5202061 A	19930413	17	Electrically conductive polymeric materials and uses thereof	252/500	438/711;
16	<input type="checkbox"/>	US 5200112 A	19930406	19	Electrically conductive polymeric materials and uses thereof	252/500	438/732
17	<input type="checkbox"/>	US 5198153 A	19930330	19	Electrically conductive polymeric	252/500	427/372.2;
18	<input type="checkbox"/>	US 5190637 A	19930302	20	Formation of microstructures by multiple level deep X-ray lithography	205/118	427/384;
19	<input type="checkbox"/>	US 4996077 A	19910226	22	Distributed ECR remote plasma processing and apparatus	427/562	428/500;
20	<input type="checkbox"/>	US 4823177 A	19890418	8	Method and device for magnetizing thin films by the use of injected spin	257/421	428/688;
21	<input type="checkbox"/>	US 4668338 A	19870526	10	Magnetron-enhanced plasma etching process	438/714	205/125
22	<input type="checkbox"/>	US 4439294 A	19840327	6	Reactive ion etching of soft-magnetic substrates	204/192.35	118/719;
23	<input type="checkbox"/>	EP 535540 A	19930407	5	Plasma etching of aluminium@-contg. layer - by using plasma formed from	204/192.37;	118/722;
24	<input checked="" type="checkbox"/>	EP 407169 A	19910109		Electron cyclotron resonance plasma	257/424	204/298.37;

Hits Details HTML

[NUM]

- ✓ L1: (264825) magnetic near3 (layer film material memory)
- ✓ L2: (5642) 1 and (plasma with (etch\$3 reactor chamber source material))
- ✓ L3: (16) 2 and (plasma with 'HCl')
- ✓ L4: (873) 2 and (chloride chloride-containing)
- ✓ L5: (873) 4 and plasma
- ✓ L6: (8) 5 and (plasma with ('HCl' hydrogen adj chloride hydrochloric))
- ✓ L7: (282) (plasma with ('HCl' hydrogen adj chloride hydrochloric)) and magnetic
- ✓ L8: (0) (plasma with ('HCl' hydrogen adj chloride hydrochloric)) and (anti adj magnetic)
- ✓ L9: (0) (plasma with ('HCl' hydrogen adj chloride hydrochloric)) and (anti-magnetic)
- ✓ L10: (0) plasma with (anti-magnetic)
- ✓ L11: (1) plasma with ('PtMn' 'IrMn')
- ✓ L12: (3) plasma with (antimagnetic)
- ✓ L13: (724) plasma with (nonmagnetic non-magnetic)
- ✓ L16: (191) plasma with (magnetoresistive magnetization)
- ✓ L17: (14) plasma with (nonferrimagnetic antiferromagnetic non-ferromagnetic)
- ✓ L18: (737) 13 or 17
- ✓ L19: (1529) (plasma with ('HCl' hydrogen adj chloride hydrochloric))
- ✓ L20: (737) plasma with (nonferrimagnetic antiferromagnetic non-ferromagnetic nonmagnetic non-...)
- ✓ L21: (16722) plasma with (ferrimagnetic magnetic magnetic magnetic resistive magnetization)
- ✓ L22: (943) 19 and (plasma with (etch\$3 reactor chamber source material gas\$2))
- ✓ L23: (943) 19 and 22
- ✓ L25: (682) 23 and (substrate wafer workpiece work adj piece)

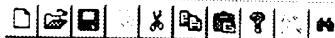


Type	Hits	Search Text	DBs	Time Stamp	Comment
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- ✓ L25: (682) 23 and (substrate wafer workpiece work adj piece)
- ✓ L26: (472) 25 and (plasma with etch\$3)
- ✓ L28: (112) 26 and (barrier)
- ✓ L29: (0) 26 and (electron adj barrier)
- ✓ L27: (17) 26 and ('NiFe' 'CoFe' 'NiFeCo' 'Ru')
- ✓ L30: (9) 27 and magnetic

Failed

	<input type="button" value="Browse"/>	<input type="button" value="Queue"/>	<input type="button" value="Clear"/>
DBs:	USPAT; US-PGPUB; EPO; JPO; DEI <input checked="" type="checkbox"/> Plusplus		
Default operator:		OR	<input checked="" type="checkbox"/> Highlight all hit terms initially
27 and magnetic			
<input type="button" value="BRS term"/> <input type="button" value="IS&R term"/> <input type="button" value="Image"/> <input type="button" value="Text"/> <input type="button" value="HTML"/>			

#	U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	R
1	<input type="checkbox"/>	<input type="checkbox"/>	US 20030013314 A1	20030116	18	Method of reducing particulates in a plasma etch chamber during a metal e	438/710		
2	<input type="checkbox"/>	<input type="checkbox"/>	US 20020129900 A1	20020919	16	Method for processing specimens, an apparatus therefor and a method of m	156/345.31	156/345.32	
3	<input type="checkbox"/>	<input type="checkbox"/>	US 20020037647 A1	20020328	55	Method of etching an anisotropic profile in platinum	438/689		
4	<input type="checkbox"/>	<input type="checkbox"/>	US 6491832 B2	20021210	15	Method for processing specimens	216/22	216/67;	
5	<input type="checkbox"/>	<input type="checkbox"/>	US 6323132 B1	20011127	52	Etching methods for anisotropic platinum profile	438/706	216/75;	
6	<input type="checkbox"/>	<input type="checkbox"/>	US 6265318 B1	20010724	47	Iridium etchant methods for anisotropic profile	438/720	438/720	
7	<input type="checkbox"/>	<input type="checkbox"/>	US 6069035 A	20000530	12	Techniques for etching a transition metal-containing layer	438/220	216/75;	
8	<input type="checkbox"/>	<input type="checkbox"/>	US 5892706 A	19990406	43	Fram, fram card, and card system using the same	365/145	365/226;	
9	<input type="checkbox"/>	<input type="checkbox"/>	US 5798964 A	19980825	43	FRAM, FRAM card, and card system using the same	365/145	365/65	
							365/149;	365/226;	

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L29: (0) 26 and (electron adj barrier)

L27: (17) 26 and ('NiFe' 'CoFe' 'NiFeCo' 'Ru')

L30: (0) 27 and magnetic

[Browse] [Queue] [Clear]

[BRS Form] [IS&R Form] [Image] [Text] [HTML]

	U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
1	<input type="checkbox"/>	<input type="checkbox"/>	US 20030037802 A1	20030227	18	Semiconductor treating apparatus and cleaning method of the same	134/1.1	118/715; 156/345.33
2	<input type="checkbox"/>	<input type="checkbox"/>	US 20030013314 A1	20030116	18	Method of reducing particulates in a plasma etch chamber during a metal etching method and cleaning method	438/710	
3	<input type="checkbox"/>	<input type="checkbox"/>	US 20020190024 A1	20021219	31	Etching method and cleaning method of chemical vapor growth apparatus	216/37	118/715; 118/724;
4	<input type="checkbox"/>	<input type="checkbox"/>	US 20020129900 A1	20020919	16	Method for processing specimens, an apparatus therefor and a method of m	156/345.31	156/345.32
5	<input type="checkbox"/>	<input type="checkbox"/>	US 20020037647 A1	20020328	55	Method of etching an anisotropic profile in platinum	438/689	
6	<input type="checkbox"/>	<input type="checkbox"/>	US 6518106 B2	20030211	7	Semiconductor device and a method therefor	438/157	257/250; 257/331;
7	<input type="checkbox"/>	<input type="checkbox"/>	US 6495054 B1	20021217	28	Etching method and cleaning method of chemical vapor growth apparatus	216/58	134/1.1; 216/63;
8	<input type="checkbox"/>	<input type="checkbox"/>	US 6491832 B2	20021210	15	Method for processing specimens	216/22	216/67; 216/75;
9	<input type="checkbox"/>	<input type="checkbox"/>	US 6410991 B1	20020625	31	Semiconductor device and method of manufacturing the same	257/392	257/607; 438/423;
10	<input type="checkbox"/>	<input type="checkbox"/>	US 6323132 B1	20011127	52	Etching methods for anisotropic platinum profile	438/706	438/710; 438/720
11	<input type="checkbox"/>	<input type="checkbox"/>	US 6265318 B1	20010724	47	Iridium etchant methods for anisotropic profile	438/720	216/67; 216/75;
12	<input type="checkbox"/>	<input type="checkbox"/>	US 6261967 B1	20010717	11	Easy to remove hard mask layer for semiconductor device fabrication	438/717	438/240; 438/393;

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L29: (0) 26 and (electron adj barrier)

L27: (17) 26 and ('NiFe' 'CoFe' 'NiFeCo' 'Ru')

L30: (0) 27 and magnetic

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HTML

	U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
6	<input type="checkbox"/>	<input type="checkbox"/>	US 6518106 B2	20030211	7	Semiconductor device and a method therefor	438/157	257/250; 257/331;
7	<input type="checkbox"/>	<input type="checkbox"/>	US 6495054 B1	20021217	28	Etching method and cleaning method of chemical vapor growth apparatus	216/58	134/1.1; 216/63;
8	<input type="checkbox"/>	<input type="checkbox"/>	US 6491832 B2	20021210	15	Method for processing specimens	216/22	216/67; 216/75;
9	<input type="checkbox"/>	<input type="checkbox"/>	US 6410991 B1	20020625	31	Semiconductor device and method of manufacturing the same	257/392	257/607; 438/423;
10	<input type="checkbox"/>	<input type="checkbox"/>	US 6323132 B1	20011127	52	Etching methods for anisotropic platinum profile	438/706	438/710; 438/720
11	<input type="checkbox"/>	<input type="checkbox"/>	US 6265318 B1	20010724	47	Iridium etchant methods for anisotropic profile	438/720	216/67; 216/75;
12	<input type="checkbox"/>	<input type="checkbox"/>	US 6261967 B1	20010717	11	Easy to remove hard mask layer for semiconductor device fabrication	438/717	438/240; 438/393;
13	<input type="checkbox"/>	<input type="checkbox"/>	US 6069035 A	20000530	12	Techniques for etching a transition metal-containing layer	438/220	438/720
14	<input type="checkbox"/>	<input type="checkbox"/>	US 5892706 A	19990406	43	Fram, fram card, and card system using the same	365/145	365/226; 365/65
15	<input type="checkbox"/>	<input type="checkbox"/>	US 5798964 A	19980825	43	FRAM, FRAM card, and card system using the same	365/145	365/149; 365/226;
16	<input type="checkbox"/>	<input type="checkbox"/>	US 5496437 A	19960305	13	Reactive ion etching of lead zirconate titanate and ruthenium oxide thin films	438/3	216/6; 216/76;
17	<input type="checkbox"/>	<input type="checkbox"/>	US 6306312 B	20020710	10	Anisotropically etching a gold layer through an aperture in hardmask invol		

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I. Number	Hits	Search Text	DB	Time stamp
1	264825	magnetic near3 (layer film material memory)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 08:34
2	5642	((magnetic near3 (layer film material memory)) and (plasma with (etch\$3 reactor chamber source material)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:28
3	16	((magnetic near3 (layer film material memory)) and (plasma with (etch\$3 reactor chamber source material))) and (plasma with HCl)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 08:47
4	873	((magnetic near3 (layer film material memory)) and (plasma with (etch\$3 reactor chamber source material))) and (chloride chloride-containing)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 08:48
5	873	((magnetic near3 (layer film material memory)) and (plasma with (etch\$3 reactor chamber source material))) and (chloride chloride-containing) and plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 08:49
6	8	(((magnetic near3 (layer film material memory)) and (plasma with (etch\$3 reactor chamber source material))) and (chloride chloride-containing)) and plasma) and (plasma with ('HCl' hydrogen adj chloride hydrochloric))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 08:51
7	282	(plasma with ('HCl' hydrogen adj chloride hydrochloric)) and magnetic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:08
8	0	(plasma with ('HCl' hydrogen adj chloride hydrochloric)) and (anti adj magnetic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 08:52
9	0	(plasma with ('HCl' hydrogen adj chloride hydrochloric)) and (anti-magnetic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 11:51
10	0	plasma with (anti-magnetic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:00
11	1	plasma with ('PtMn' 'IrMn')	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 08:54
12	3	plasma with (antimagnetic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:01

1	Number	Hits	Search Text	DB	Time stamp
1		264825	magnetic near3 (layer film material memory)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 08:34
2		5642	((magnetic near3 (layer film material memory)) and (plasma with (etch\$3 reactor chamber source material)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:28
3		16	((magnetic near3 (layer film material memory)) and (plasma with (etch\$3 reactor chamber source material))) and (plasma with HCl)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 08:47
4		873	((magnetic near3 (layer film material memory)) and (plasma with (etch\$3 reactor chamber source material))) and (chloride chloride-containing)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 08:48
5		873	((magnetic near3 (layer film material memory)) and (plasma with (etch\$3 reactor chamber source material))) and (chloride chloride-containing)) and plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 08:49
6		8	(((magnetic near3 (layer film material memory)) and (plasma with (etch\$3 reactor chamber source material))) and (chloride chloride-containing)) and plasma) and (plasma with ('HCl' hydrogen adj chloride hydrochloric))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 08:51
7		282	(plasma with ('HCl' hydrogen adj chloride hydrochloric)) and magnetic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:08
8		0	(plasma with ('HCl' hydrogen adj chloride hydrochloric)) and (anti adj magnetic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 08:52
9		0	(plasma with ('HCl' hydrogen adj chloride hydrochloric)) and (anti-magnetic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 08:53
10		0	plasma with (anti-magnetic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:00
11		1	plasma with ('PtMn' 'IrMn')	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 08:54
12		3	plasma with (antimagnetic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:01

13	724	plasma with (nonmagnetic non-magnetic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:02
16	191	plasma with (magnetoresistive magnetization)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:06
17	14	plasma with (nonferrmagnetic antiferromagnetic non-ferromagnetic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:16
18	737	((plasma with (nonmagnetic non-magnetic)) or (plasma with (nonferrmagnetic antiferromagnetic non-ferromagnetic)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:06
19	1529	((plasma with ('HCl' hydrogen adj chloride hydrochloric)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:08
20	737	plasma with (nonferrmagnetic antiferromagnetic non-ferromagnetic nonmagnetic non-magnetic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:17
21	16722	plasma with (ferrmagnetic magnetic magnetic magneticresistive magnetization)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:19
22	943	((plasma with ('HCl' hydrogen adj chloride hydrochloric)) and (plasma with (etch\$3 reactor chamber source material gas\$2)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:30
23	943	(((plasma with ('HCl' hydrogen adj chloride hydrochloric)) and ((plasma with ('HCl' hydrogen adj chloride hydrochloric)) and (plasma with (etch\$3 reactor chamber source material gas\$2))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:31
25	682	(((plasma with ('HCl' hydrogen adj chloride hydrochloric)) and ((plasma with ('HCl' hydrogen adj chloride hydrochloric)) and (plasma with (etch\$3 reactor chamber source material gas\$2)))) and (substrate wafer workpiece work adj piece))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:32

13	724	plasma with (nonmagnetic non-magnetic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:02
16	191	plasma with (magnetoresistive magnetization)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:06
17	14	plasma with (nonferrimagnetic antiferromagnetic non-ferromagnetic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:16
18	737	(plasma with (nonmagnetic non-magnetic)) or (plasma with (nonferrimagnetic antiferromagnetic non-ferromagnetic))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:06
19	1529	(plasma with ('HCl' hydrogen adj chloride hydrochloric))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 11:58
20	737	plasma with (nonferrimagnetic antiferromagnetic non-ferromagnetic nonmagnetic non-magnetic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 11:49
21	16722	plasma with (ferrimagnetic magnetic magnetic magneticresistive magnetization)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:19
22	943	((plasma with ('HCl' hydrogen adj chloride hydrochloric))) and (plasma with (etch\$3 reactor chamber source material gas\$2))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:30
23	943	((plasma with ('HCl' hydrogen adj chloride hydrochloric))) and ((plasma with ('HCl' hydrogen adj chloride hydrochloric))) and (plasma with (etch\$3 reactor chamber source material gas\$2)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:31
25	682	(((plasma with ('HCl' hydrogen adj chloride hydrochloric))) and ((plasma with ('HCl' hydrogen adj chloride hydrochloric))) and (plasma with (etch\$3 reactor chamber source material gas\$2)))) and (substrate wafer workpiece work adj piece)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:39
26	472	(((plasma with ('HCl' hydrogen adj chloride hydrochloric))) and ((plasma with ('HCl' hydrogen adj chloride hydrochloric))) and (plasma with (etch\$3 reactor chamber source material gas\$2)))) and (substrate wafer workpiece work adj piece)) and (plasma with etch\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:43
28	112	((((plasma with ('HCl' hydrogen adj chloride hydrochloric))) and ((plasma with ('HCl' hydrogen adj chloride hydrochloric))) and (plasma with (etch\$3 reactor chamber source material gas\$2)))) and (substrate wafer workpiece work adj piece)) and (plasma with etch\$3)) and (barrier)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:45

27	17	(((((plasma with ('HCl' hydrogen adj chloride hydrochloric))) and (((plasma with ('HCl' hydrogen adj chloride hydrochloric))) and (plasma with (etch\$3 reactor chamber source material gas\$2))) and (substrate wafer workpiece work adj piece)) and (plasma with etch\$3)) and ('NiFe' 'CoFe' 'NiFeCo' 'Ru'))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 11:03
30	9	(((((plasma with ('HCl' hydrogen adj chloride hydrochloric))) and (((plasma with ('HCl' hydrogen adj chloride hydrochloric))) and (plasma with (etch\$3 reactor chamber source material gas\$2))) and (substrate wafer workpiece work adj piece)) and (plasma with etch\$3)) and ('NiFe' 'CoFe' 'NiFeCo' 'Ru')) and magnetic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:47
36	1	(((plasma with ('HCl' hydrogen adj chloride hydrochloric))) and ((plasma with (nonferrmagnetic antiferromagnetic non-ferromagnetic nonmagnetic non-magnetic))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 11:04
37	1	(((plasma with ('HCl' hydrogen adj chloride hydrochloric))) and ((plasma with (nonferrmagnetic antiferromagnetic non-ferromagnetic nonmagnetic non-magnetic))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 11:08
38	738	plasma with (nonferrmagnetic antiferromagnetic non-ferromagnetic nonmagnetic non-magnetic anti-ferromagnetic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 11:52
39	1	(((plasma with ('HCl' hydrogen adj chloride hydrochloric))) and ((plasma with (nonferrmagnetic antiferromagnetic non-ferromagnetic nonmagnetic non-magnetic anti-ferromagnetic))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 11:50
40	1	(((plasma with (nonferrmagnetic antiferromagnetic non-ferromagnetic nonmagnetic non-magnetic anti-ferromagnetic)) with ('HCl' hydrogen adj chloride hydrochloric)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 11:53
41	1	(((nonferrmagnetic antiferromagnetic non-ferromagnetic nonmagnetic non-magnetic anti-ferromagnetic anti-magnetic) with ('HCl' hydrogen adj chloride hydrochloric) with plasma)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 11:55
42	1	(((nonferrmagnetic antiferromagnetic non-ferromagnetic nonmagnetic non-magnetic anti-ferromagnetic anti-magnetic) with ('HCl' hydrogen adj chloride hydrochloric) with plasma)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 11:56
43	738	(((nonferrmagnetic antiferromagnetic non-ferromagnetic nonmagnetic non-magnetic anti-ferromagnetic anti-magnetic) with plasma)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 11:56
44	1529	(((plasma with ('HCl' hydrogen adj chloride hydrochloric))) and ((plasma with ('HCl' hydrogen adj chloride hydrochloric)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 11:59
45	1	(((nonferrmagnetic antiferromagnetic non-ferromagnetic nonmagnetic non-magnetic anti-ferromagnetic anti-magnetic) with plasma) and ((plasma with ('HCl' hydrogen adj chloride hydrochloric)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 11:59

1 Number	1 Hits	Search Text	DB	Time stamp
1	264825	magnetic near3 (layer film material memory)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 08:34
2	5642	((magnetic near3 (layer film material memory)) and (plasma with (etch\$3 reactor chamber source material)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:28
3	16	((magnetic near3 (layer film material memory)) and (plasma with (etch\$3 reactor chamber source material))) and (plasma with HCl)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 08:47
4	873	((magnetic near3 (layer film material memory)) and (plasma with (etch\$3 reactor chamber source material))) and (chloride chloride-containing)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 08:48
5	873	((magnetic near3 (layer film material memory)) and (plasma with (etch\$3 reactor chamber source material))) and (chloride chloride-containing) and plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 08:49
6	8	((magnetic near3 (layer film material memory)) and (plasma with (etch\$3 reactor chamber source material))) and (chloride chloride-containing) and plasma and (plasma with ('HCl' hydrogen adj chloride hydrochloric))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 08:51
7	282	(plasma with ('HCl' hydrogen adj chloride hydrochloric)) and magnetic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:08
8	0	(plasma with ('HCl' hydrogen adj chloride hydrochloric)) and (anti adj magnetic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 08:52
9	0	(plasma with ('HCl' hydrogen adj chloride hydrochloric)) and (anti-magnetic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 11:51
10	0	plasma with (anti-magnetic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:00
11	1	plasma with ('PtMn' 'IrMn')	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 08:54
12	3	plasma with (antimagnetic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:01

13	724	plasma with (nonmagnetic non-magnetic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:02
16	191	plasma with (magnetoresistive magnetization)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:06
17	14	plasma with (nonferrimagnetic antiferromagnetic non-ferromagnetic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:16
18	737	(plasma with (nonmagnetic non-magnetic)) or (plasma with (nonferrimagnetic antiferromagnetic non-ferromagnetic))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:06
19	1529	(plasma with ('HCl' hydrogen adj chloride hydrochloric))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 11:58
20	737	plasma with (nonferrimagnetic antiferromagnetic non-ferromagnetic nonmagnetic non-magnetic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 11:49
21	16722	plasma with (ferrimagnetic magnetic magnetic magneticresistive magnetization)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:19
22	943	((plasma with ('HCl' hydrogen adj chloride hydrochloric))) and (plasma with (etch\$3 reactor chamber source material gas\$2))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:30
23	943	((plasma with ('HCl' hydrogen adj chloride hydrochloric))) and ((plasma with ('HCl' hydrogen adj chloride hydrochloric))) and (plasma with (etch\$3 reactor chamber source material gas\$2)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:31
25	682	((plasma with ('HCl' hydrogen adj chloride hydrochloric))) and ((plasma with ('HCl' hydrogen adj chloride hydrochloric))) and (plasma with (etch\$3 reactor chamber source material gas\$2))) and (substrate wafer workpiece work adj piece)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:39
26	472	((((plasma with ('HCl' hydrogen adj chloride hydrochloric))) and ((plasma with ('HCl' hydrogen adj chloride hydrochloric))) and (plasma with (etch\$3 reactor chamber source material gas\$2)))) and (substrate wafer workpiece work adj piece)) and (plasma with etch\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:43
28	112	(((plasma with ('HCl' hydrogen adj chloride hydrochloric))) and ((plasma with ('HCl' hydrogen adj chloride hydrochloric))) and (plasma with (etch\$3 reactor chamber source material gas\$2)))) and (substrate wafer workpiece work adj piece)) and (plasma with etch\$3)) and (barrier)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:45

27	17	((((plasma with ('HCl' hydrogen adj chloride hydrochloric))) and ((plasma with ('HCl' hydrogen adj chloride hydrochloric))) and (plasma with (etch\$3 reactor chamber source material gas\$2))) and (substrate wafer workpiece work adj piece)) and (plasma with etch\$3)) and ('NiFe' 'CoFe' 'NiFeCo' 'Ru'))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 12:30
30	9	(((((plasma with ('HCl' hydrogen adj chloride hydrochloric))) and (((plasma with ('HCl' hydrogen adj chloride hydrochloric))) and (plasma with (etch\$3 reactor chamber source material gas\$2))) and (substrate wafer workpiece work adj piece)) and (plasma with etch\$3)) and ('NiFe' 'CoFe' 'NiFeCo' 'Ru')) and magnetic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:47
36	1	(((plasma with ('HCl' hydrogen adj chloride hydrochloric))) and (plasma with (nonferrmagnetic antiferromagnetic non-ferromagnetic nonmagnetic non-magnetic))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 11:04
37	1	(((plasma with ('HCl' hydrogen adj chloride hydrochloric))) and (plasma with (nonferrmagnetic antiferromagnetic non-ferromagnetic nonmagnetic non-magnetic))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 11:08
38	738	plasma with (nonferrmagnetic antiferromagnetic non-ferromagnetic nonmagnetic non-magnetic anti-ferromagnetic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 11:52
39	1	(((plasma with ('HCl' hydrogen adj chloride hydrochloric))) and (plasma with (nonferrmagnetic antiferromagnetic non-ferromagnetic nonmagnetic non-magnetic anti-ferromagnetic))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 11:50
40	1	(((plasma with (nonferrmagnetic antiferromagnetic non-ferromagnetic nonmagnetic non-magnetic anti-ferromagnetic)) with ('HCl' hydrogen adj chloride hydrochloric)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 11:53
41	1	(((nonferrmagnetic antiferromagnetic non-ferromagnetic nonmagnetic non-magnetic anti-ferromagnetic anti-magnetic) with ('HCl' hydrogen adj chloride hydrochloric) with plasma)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 11:55
42	1	(((nonferrmagnetic antiferromagnetic non-ferromagnetic nonmagnetic non-magnetic anti-ferromagnetic anti-magnetic) with ('HCl' hydrogen adj chloride hydrochloric) with plasma)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 11:56
43	738	(((nonferrmagnetic antiferromagnetic non-ferromagnetic nonmagnetic non-magnetic anti-ferromagnetic anti-magnetic) with plasma)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 12:13
44	1529	(((plasma with ('HCl' hydrogen adj chloride hydrochloric))) and (plasma with ('HCl' hydrogen adj chloride hydrochloric))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 12:00
45	1	(((nonferrmagnetic antiferromagnetic non-ferromagnetic nonmagnetic non-magnetic anti-ferromagnetic anti-magnetic) with plasma) and (plasma with ('HCl' hydrogen adj chloride hydrochloric))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 12:00

46	1	(nonferromagnetic antiferromagnetic non-ferromagnetic nonmagnetic non-magnetic anti-ferromagnetic anti-magnetic) with plasma) and ((plasma with ('HCl' hydrogen adj chloride hydrochloric)) and (plasma with ('HCl' hydrogen adj chloride hydrochloric))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 12:00
47	1529	(plasma with ('HCl' hydrogen adj chloride hydrochloric))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 12:34
49	34	((plasma with ('HCl' hydrogen adj chloride hydrochloric)) and (nonferromagnetic antiferromagnetic non-ferromagnetic nonmagnetic non-magnetic anti-ferromagnetic anti-magnetic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 12:32
50	0	((plasma with ('HCl' hydrogen adj chloride hydrochloric)) and ('PtMn' 'IrMn')	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 12:24
51	694	('PtMn' 'IrMn')	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 12:25
52	1	('PtMn' 'IrMn') with plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 12:25
53	45	((plasma with ('HCl' hydrogen adj chloride hydrochloric)) and ('NiFe' 'CoFe' 'NiFeCo' 'Ru')	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 12:30
54	34	((plasma with ('HCl' hydrogen adj chloride hydrochloric)) and (nonferromagnetic antiferromagnetic non-ferromagnetic nonmagnetic non-magnetic anti-ferromagnetic anti-magnetic antimagnetic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 12:33
55	4427	plasma and (nonferromagnetic antiferromagnetic non-ferromagnetic nonmagnetic non-magnetic anti-ferromagnetic anti-magnetic antimagnetic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 12:33
56	34	(plasma and (nonferromagnetic antiferromagnetic non-ferromagnetic nonmagnetic non-magnetic anti-ferromagnetic anti-magnetic antimagnetic)) and (plasma with ('HCl' hydrogen adj chloride hydrochloric))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 12:46